

Date Mailed: OCTOBER 4, 2006

Sheet 1 of 1

FORM 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)	Docket Number: 14434.103USWO	Application Number: UNKNOWN
	Applicant: TAKEUCHI et al.	
	Filing Date: concurrent herewith	Group Art Unit: UNKNOWN

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
	2005/0079659	4.14.05	DUAN et al.				
	2005/0056828	3.17.05	WADA et al.				
	6,108,956	1.30.2001	CHONDROUDIS et al.				
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	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	2004/032193	15.04.2004	WIPO				
	2004-111870	2004.04.08	JP			ABSTRACT	
	2004-067413	2004.03.04	JP			ABSTRACT	
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
		Duan et al., High-performance thin-film transistors using semiconductor nanowires and nanoribbons, Nature Vol. 425, September 18, 2003, pp. 274-278 *					
		Morales et al., A laser ablation method for the synthesis of crystalline semiconductor nanowires, Science Vol. 279, January 9, 1998, pp. 208-211 *					
		Lew et al., Growth characteristics of silicon nanowires synthesized by vapor-liquid-solid growth in nanoporous alumina templates, Journal of Crystal Growth Vol. 254, 2003, pp. 14-22 *					
		Greytak et al., Growth and transport properties of complementary germanium nanowire field-effect transistors, Applied Physics Letters Vol. 84, No. 21, May 24, 2004, pp. 4176-4178 *					

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PATENT TRADEMARK OFFICE

EXAMINER /Eva Montalvo/	DATE CONSIDERED 11/26/2008
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.	